

Yvon CORDIER - CV

Yvon Cordier was graded as engineer in materials science in 1988. He received the Ph.D. degree from the University of Lille in 1992. He worked at Thomson-CSF Central Research Laboratory, Orsay, for five years where he was in charge of the epitaxy of III-V heterostructures for electronic and optoelectronic devices. In 1996, he was engaged by CNRS at the Institut d'Electronique, de Microélectronique et de Nanotechnologie (IEMN) where he developed and studied InAlAs/InGaAs metamorphic HEMTs on GaAs substrate. In 2001, he joined the Centre de Recherche sur l'Hétéro-Epitaxie et ses Applications (CRHEA) to develop Gallium Nitride epitaxy for electronics. Since 2010, he's leading a research group where III-Nitrides and other semiconductor compounds like SiC, ZnO and 2D materials are developed and studied.